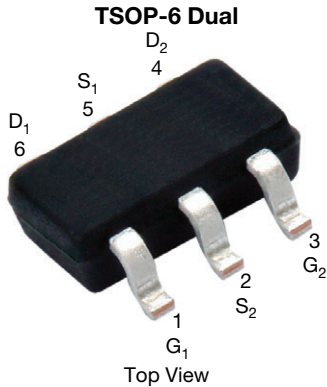




**THE DATASHEET OF
SQ3585EV-T1_GE3**



Automotive N- and P-Channel 20 V (D-S) MOSFET



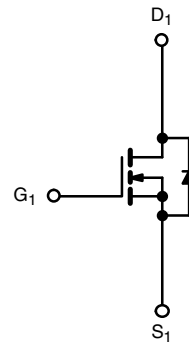
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

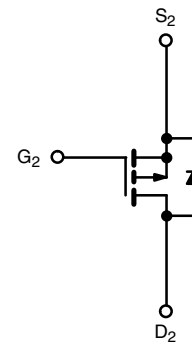
 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE

PRODUCT SUMMARY		
	N-CHANNEL	P-CHANNEL
V _{DS} (V)	20	-20
R _{DS(on)} (Ω) at V _{GS} = ± 4.5 V	0.077	0.166
R _{DS(on)} (Ω) at V _{GS} = ± 2.5 V	0.120	0.318
I _D (A)	3.57	-2.5
Configuration	N- and p-pair	



N-Channel MOSFET



P-Channel MOSFET

ORDERING INFORMATION	
Package	TSOP-6 Dual
Lead (Pb)-free and halogen-free	SQ3585EV (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
Drain-source voltage	V _{DS}	20	-20	V
Gate-source voltage	V _{GS}	± 12	± 12	
Continuous drain current	I _D	T _C = 25 °C	3.57	A
		T _C = 125 °C	2	
Pulsed drain current	I _{DM}	12	-10	A
Continuous source current (diode conduction)	I _S	2.1	-2.1	
Maximum power dissipation	P _D	T _C = 25 °C	1.67	W
		T _C = 125 °C	0.56	
Unclamped inductive surge UIS	I _{AV}	3.3	3	A
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +175		°C

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
		MAX.	MAX.	
Maximum junction-to-ambient ^a	Steady state	R _{thJA}	150	°C/W
Maximum junction-to-foot (drain)	Steady state	R _{thJF}	90	

Note

a. Surface mounted on 1" x 1" FR4 board



SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		N-Ch	0.6	-	1.5	V
		$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$		P-Ch	-0.6	-	-1.5	
Gate-body leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$		N-Ch	-	-	± 100	nA
				P-Ch	-	-	± 100	
Zero gate voltage drain current	I_{DSS}	$V_{GS} = 0 \text{ V}$	$V_{DS} = 20 \text{ V}$	N-Ch	-	-	1	μA
		$V_{GS} = 0 \text{ V}$	$V_{DS} = -20 \text{ V}$	P-Ch	-	-	-1	
		$V_{GS} = 0 \text{ V}$	$V_{DS} = 20 \text{ V}, T_J = 55^\circ\text{C}$	N-Ch	-	-	5	
		$V_{GS} = 0 \text{ V}$	$V_{DS} = -20 \text{ V}, T_J = 55^\circ\text{C}$	P-Ch	-	-	-5	
On-state drain current ^a	$I_{D(on)}$	$V_{GS} = 4.5 \text{ V}$	$V_{DS} \geq 5 \text{ V}$	N-Ch	5	-	-	A
		$V_{GS} = -4.5 \text{ V}$	$V_{DS} \leq -5 \text{ V}$	P-Ch	-5	-	-	
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 4.5 \text{ V}$	$I_D = 1 \text{ A}$	N-Ch	-	0.049	0.077	Ω
		$V_{GS} = -4.5 \text{ V}$	$I_D = -1 \text{ A}$	P-Ch	-	0.140	0.166	
		$V_{GS} = 2.5 \text{ V}$	$I_D = 1 \text{ A}$	N-Ch	-	0.066	0.120	
		$V_{GS} = -2.5 \text{ V}$	$I_D = -1 \text{ A}$	P-Ch	-	0.265	0.318	
Forward transconductance ^a	g_{fs}	$V_{DS} = 5 \text{ V}, I_D = 1 \text{ A}$		N-Ch	-	10	-	S
		$V_{DS} = -5 \text{ V}, I_D = -1 \text{ A}$		P-Ch	-	3	-	
Diode forward voltage ^a	V_{SD}	$I_S = 1.05 \text{ A}, V_{GS} = 0 \text{ V}$		N-Ch	-	0.80	1.10	V
		$I_S = -1.05 \text{ A}, V_{GS} = 0 \text{ V}$		P-Ch	-	-0.83	-1.10	
Dynamic ^b								
Total gate charge	Q_g	$V_{GS} = 4.5 \text{ V}$	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ A}$	N-Ch	-	1.8	2.5	nC
		$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ A}$	P-Ch	-	2.4	3.5	
Gate-source charge	Q_{gs}	$V_{GS} = 4.5 \text{ V}$	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ A}$	N-Ch	-	0.3	-	nC
		$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ A}$	P-Ch	-	0.4	-	
Gate-drain charge	Q_{gd}	$V_{GS} = 4.5 \text{ V}$	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ A}$	N-Ch	-	0.4	-	nC
		$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ A}$	P-Ch	-	0.7	-	
Gate resistance	R_g	$f = 1 \text{ MHz}$		N-Ch	3.4	-	9.1	Ω
				P-Ch	3.4	-	9.1	
Turn-on delay time	$t_{d(on)}$	N-Channel $V_{DD} = 10 \text{ V}, R_L = 10 \Omega$ $I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \text{ k}\Omega$		N-Ch	-	9	12	ns
Rise time	t_r			P-Ch	-	7	11	
				N-Ch	-	15	19	
Turn-off delay time	$t_{d(off)}$			P-Ch	-	16	22	
		P-Channel $V_{DD} = -10 \text{ V}, R_L = 10 \Omega$ $I_D \cong -1 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \text{ k}\Omega$		N-Ch	-	22	28	
Fall time	t_f			P-Ch	-	29	40	
				N-Ch	-	8	12	
				P-Ch	-	14	24	

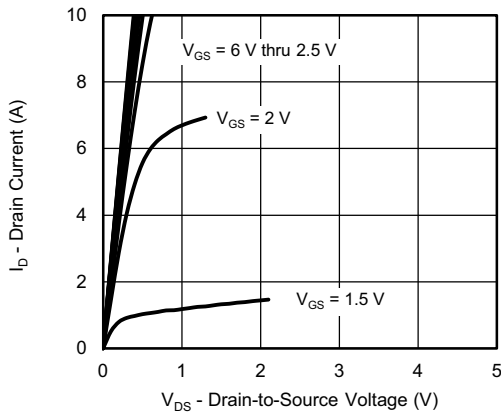
Notes

- a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2 \%$
- b. Guaranteed by design, not subject to production testing

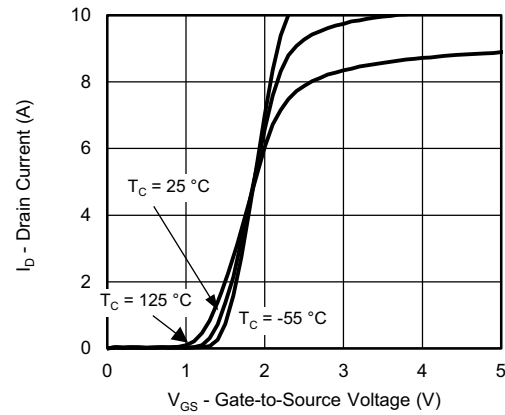
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



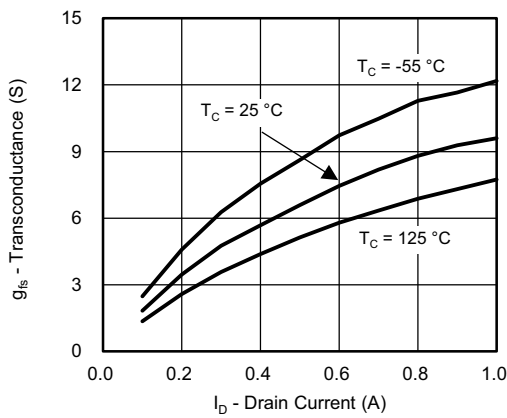
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



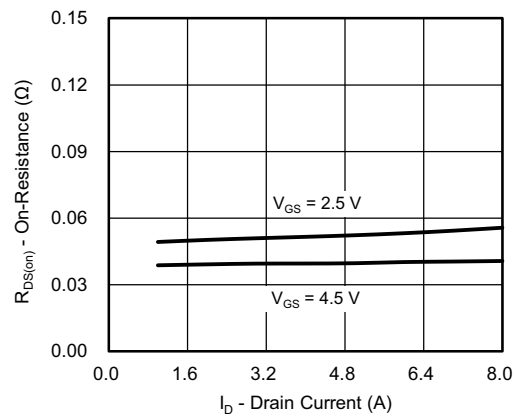
Output Characteristics



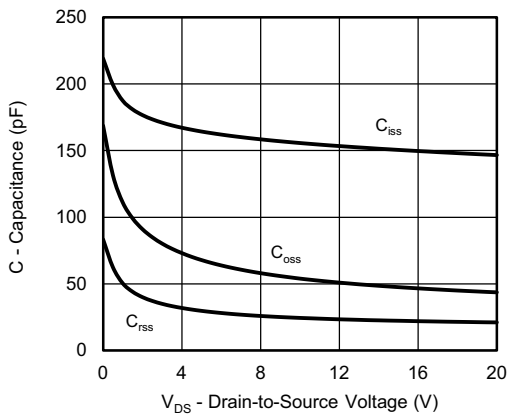
Transfer Characteristics



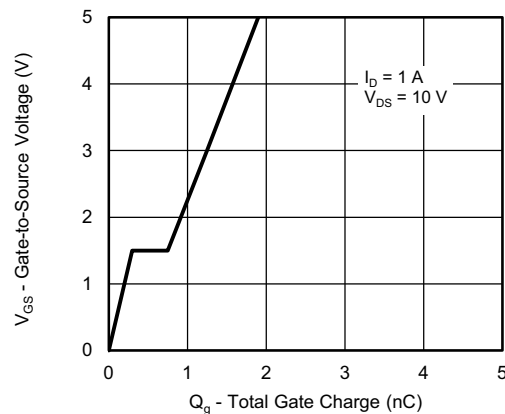
Transconductance



On-Resistance vs. Drain Current



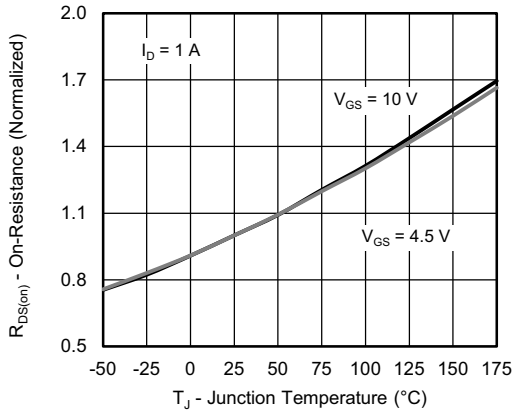
Capacitance



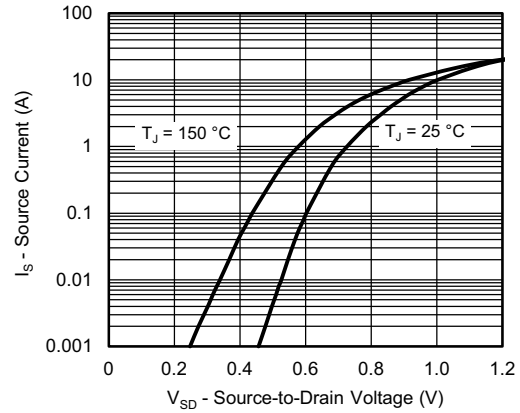
Gate Charge



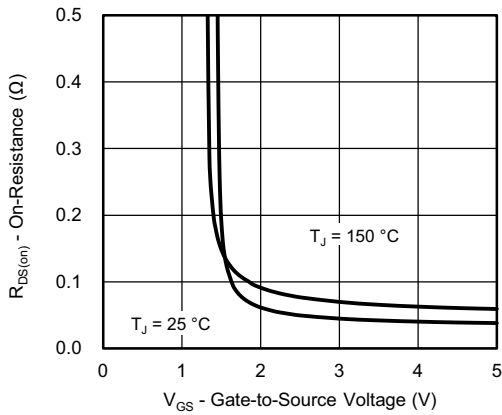
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



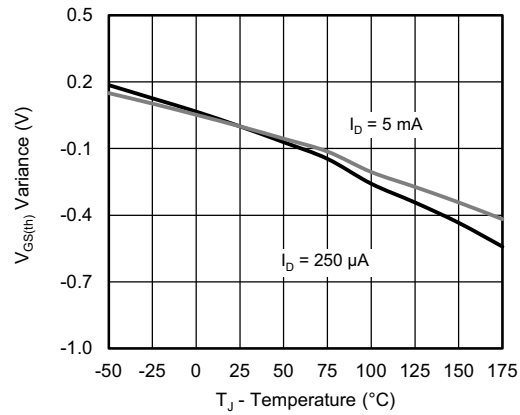
On-Resistance vs. Junction Temperature



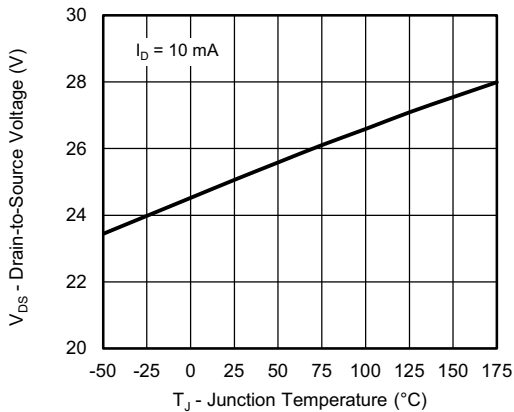
Source-Drain Diode Forward Voltage



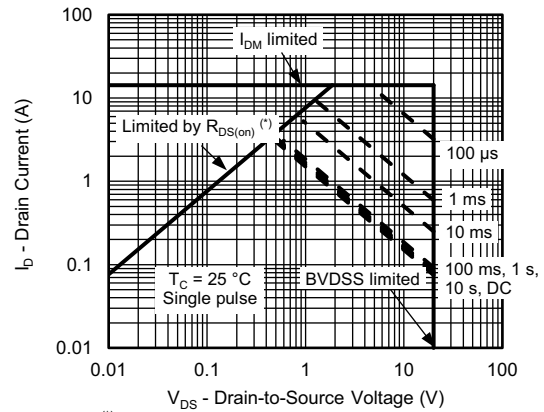
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



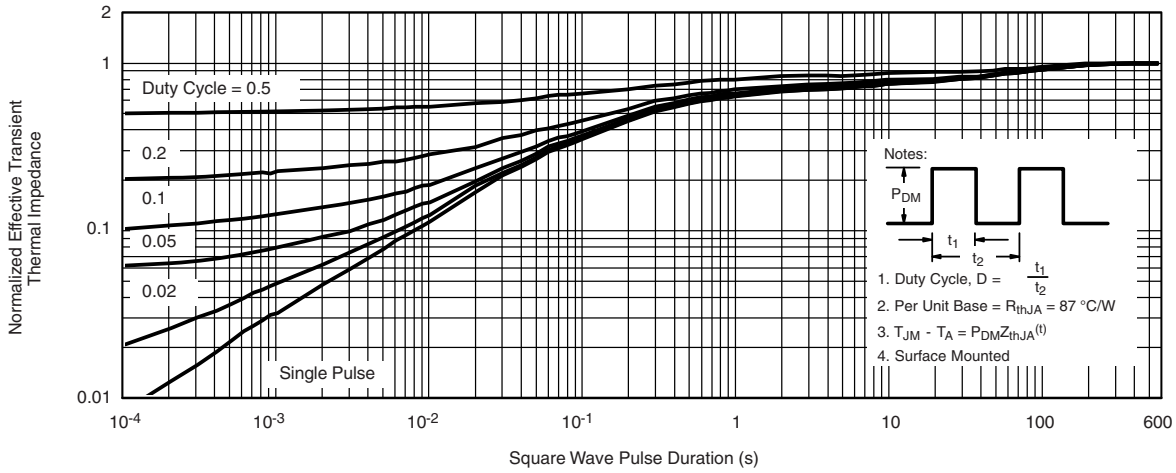
Drain Source Breakdown vs. Junction Temperature



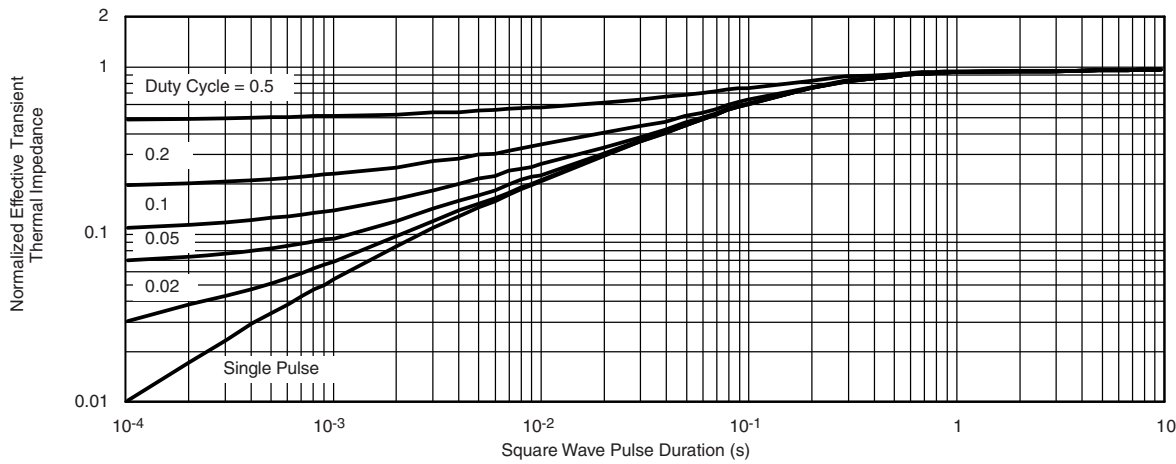
Safe Operating Area



N-CHANNEL TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)

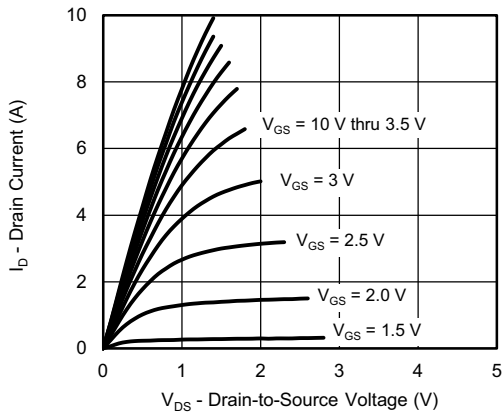


Normalized Thermal Transient Impedance, Junction-to-Ambient

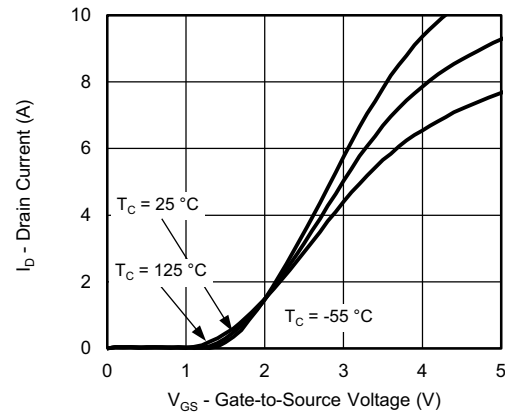


Normalized Thermal Transient Impedance, Junction-to-Foot

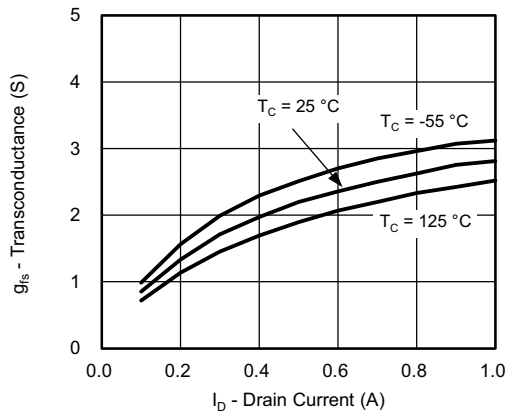
P-CHANNEL TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



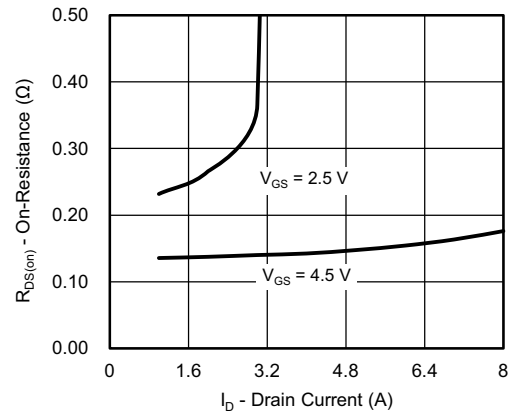
Output Characteristics



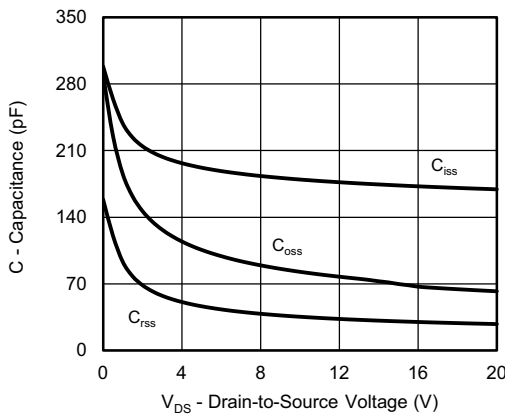
Transfer Characteristics



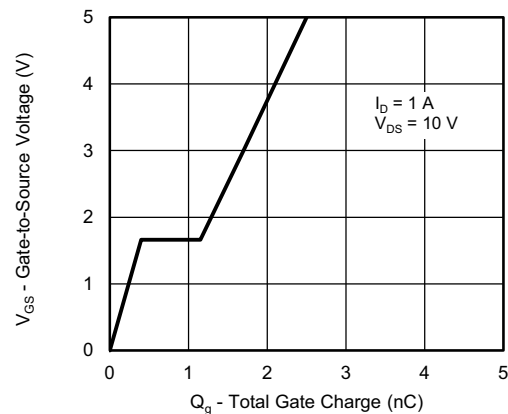
Transconductance



On-Resistance vs. Drain Current

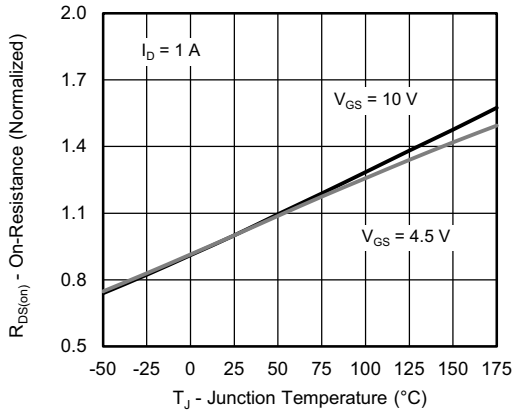


Capacitance

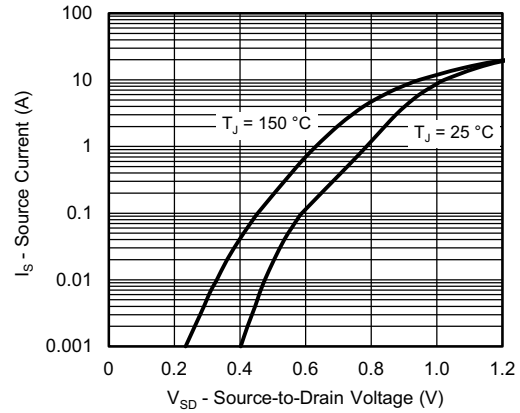


Gate Charge

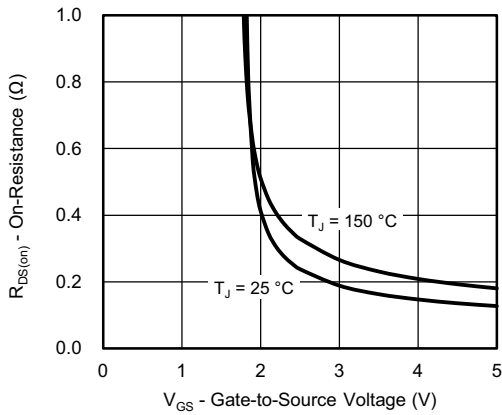
P-CHANNEL TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



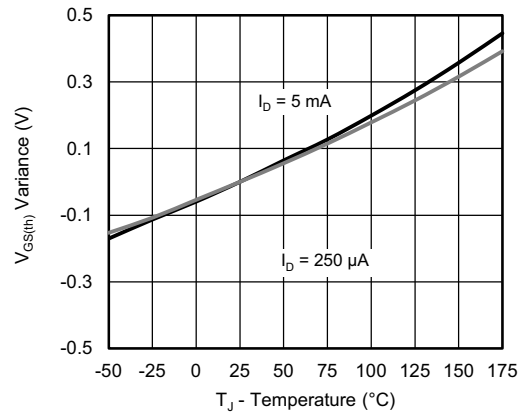
On-Resistance vs. Junction Temperature



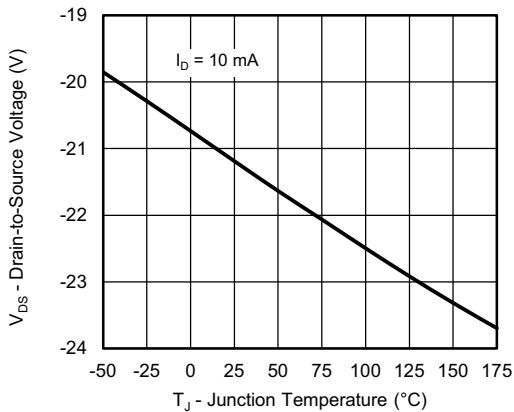
Source-Drain Diode Forward Voltage



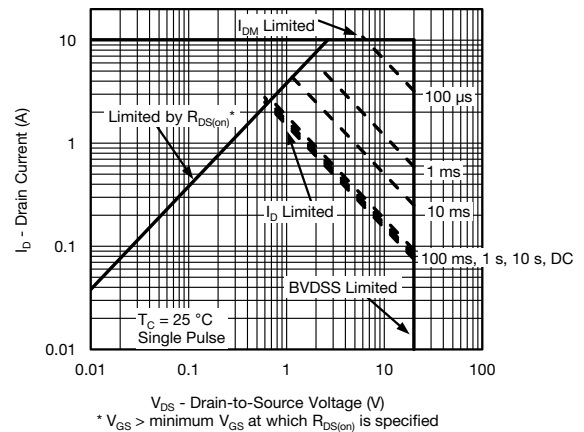
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



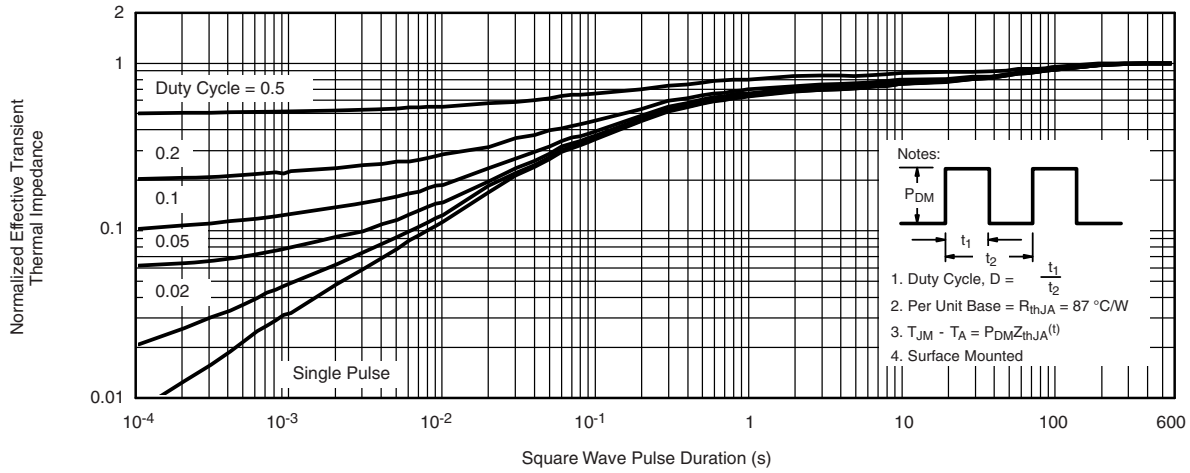
Drain Source Breakdown vs. Junction Temperature



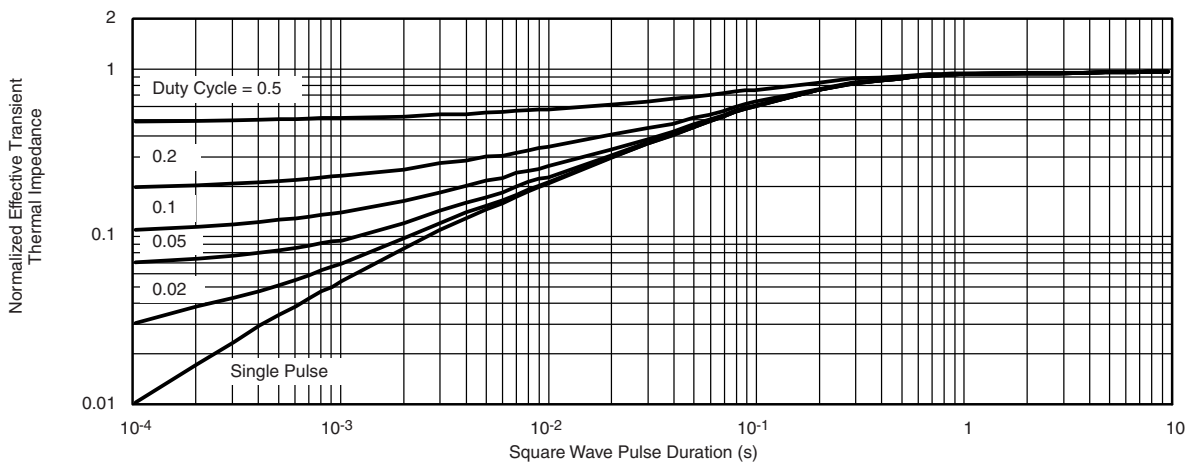
Safe Operating Area



P-CHANNEL TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



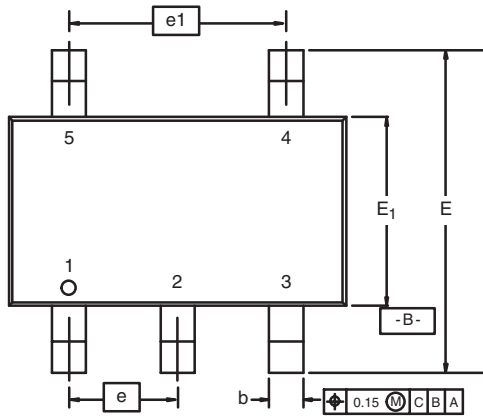
Normalized Thermal Transient Impedance, Junction-to-Foot

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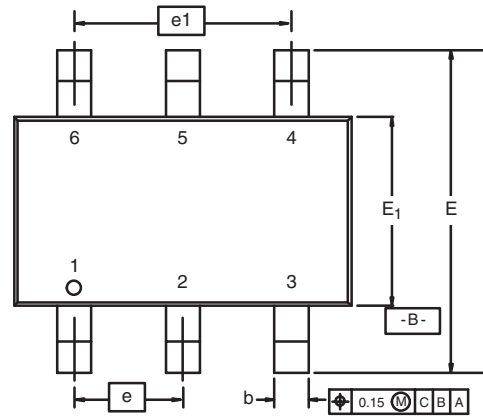


TSOP: 5/6-LEAD

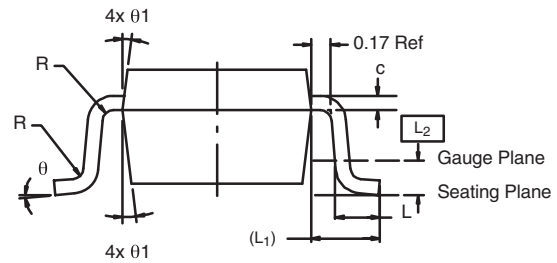
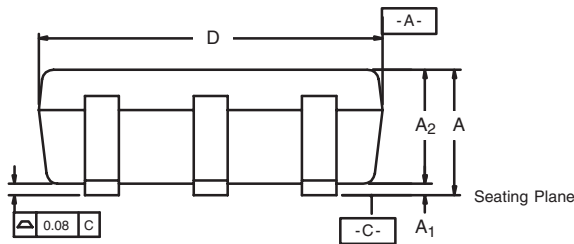
JEDEC Part Number: MO-193C



5-LEAD TSOP



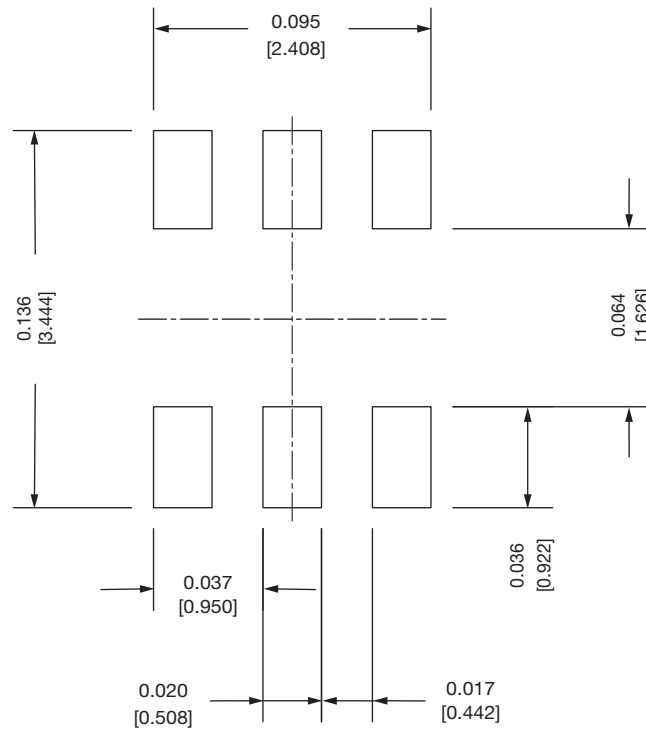
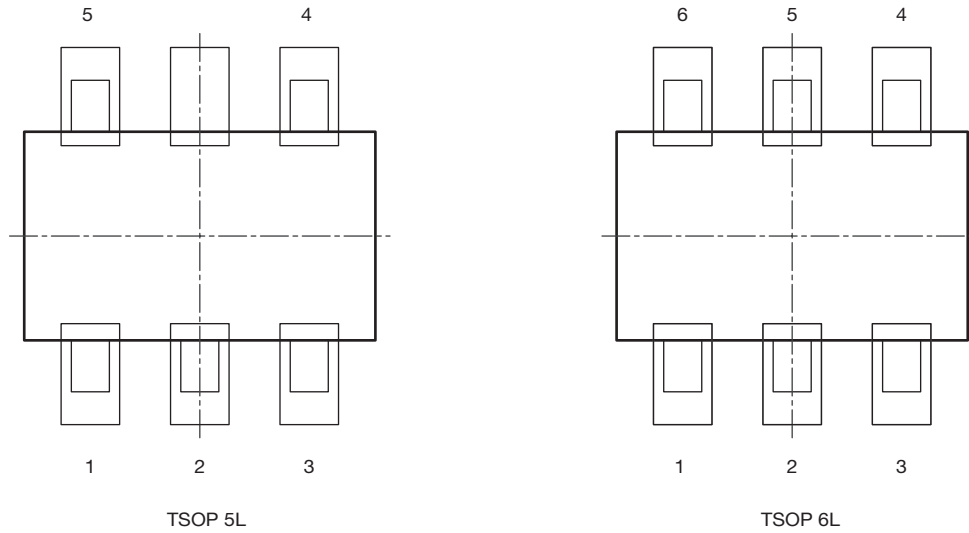
6-LEAD TSOP



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e ₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L ₁	0.60 Ref			0.024 Ref		
L ₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ ₁	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						



Recommended Land Pattern For TSOP-5L / TSOP-6L



Note

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022
 DWG: 3010



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